

ABSTRACT

The present invention provides a structure for a semiconductor device, capable of eliminating the generation of defective products due to poor connection. In the present semiconductor device, an n-type high concentration diffusion layer 2 is selectively formed on the P-type silicon substrate 1, and on the diffusion layer 2, a silicon oxide film 3 is formed as a first interlayer insulating film 3. A silicon plug 4 is disposed on the n-type high concentration diffusion layer 2. On the top end surface of the polysilicon plug 4, a silicide pad 5 is formed in a self-aligning manner such that the width of the silicide pad 5 is larger than that of the polysilicon plug 4. A second interlayer insulating film is formed so as to cover the first interlayer insulating film 3 and the silicide pad 5, and a tungsten plug 7 is disposed on the silicide pad 5. On the second interlayer insulating film, wiring 8, made of an aluminum-copper alloy and connected to the tungsten plug, is formed.